

Charge collection studies on heavily irradiated diodes from the RD50 multiplication run (an update)

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Special diodes were designed on RD50 multiplication mask which combine the ease of use of a pad-detector with electric field of a strip detector. A series of charge collection measurements was performed with diodes of different implant properties and thicknesses. The diodes were irradiated with neutrons to the total accumulated fluence of $8 \times 10^{16} \text{ cm}^{-2}$. Charge collection efficiency for ^{90}Sr was measured at each fluence and for selected detectors also during long term annealing. The values were compared between the wafers with different properties as well as with standard pad detectors.

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